



# **N-Channel 150V Power MOSFET**

## **FEATURES**

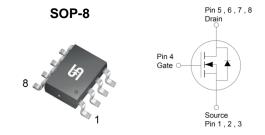
- Low R<sub>DS(ON)</sub> to minimize conductive losses
- Low gate charge for fast power switching
- RoHS Compliant
- Halogen-Free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
V <sub>DS</sub>		150	V	
R <sub>DS(on)</sub> (max)	$V_{GS} = 10V$	50	mΩ	

## **APPLICATIONS**

- DC-DC Converters
- Power Routing
- Motor Drives





Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		$V_{DS}$	150	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current	$T_C = 25^{\circ}C$		11	^
	$T_A = 25$ °C	I <sub>D</sub>	4	A
Pulsed Drain Current		I <sub>DM</sub>	44	Α
Single Pulse Avalanche Current		I <sub>AS</sub>	8.9	А
Single Pulse Avalanche Energy		E <sub>AS</sub>	12	mJ
Total Power Dissipation	T <sub>A</sub> = 25°C	P <sub>D</sub>	12.7	W
Operating Junction and Storage Tel	mperature Range	T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Thermal Resistance – Junction to Case	R <sub>⊖</sub> Jc	9.85	°C/W	
Thermal Resistance – Junction to Ambient	$R_{\Theta JA}$	75	°C/W	

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PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static		1			l	1
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	150			V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	V <sub>GS(TH)</sub>	2	3	4	V
Gate-Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Drain-Source Leakage Current	$V_{GS} = 0V, V_{DS} = 120V$	I <sub>DSS</sub>		1	μA	
	$V_{GS} = 0V, V_{DS} = 120V$ $T_{J} = 125^{\circ}C$			10		
Drain-Source On-State Resistance (Note 3)	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4A	R <sub>DS(on)</sub>		40.6	50	mΩ
Forward Transconductance (Note 3)	$V_{DS} = 10V, I_{D} = 4A$	g <sub>fs</sub>		22		S
Dynamic (Note 4)		1		1		•
Total Gate Charge		Qg		20.5		
Gate-Source Charge	$V_{GS} = 10V, V_{DS} = 80V,$ $I_{D} = 4A$	$Q_{gs}$		4.6		nC
Gate-Drain Charge		$Q_{gd}$		6		
Total Gate Charge		Qg		15.6		
Gate-Source Charge	$V_{GS} = 7V, V_{DS} = 80V,$	$Q_gs$		4.5		nC
Gate-Drain Charge	$I_D = 4A$	$Q_{gd}$		6		
Input Capacitance		C <sub>iss</sub>	-	1123		
Output Capacitance	$V_{GS} = 0V, V_{DS} = 80V,$	C <sub>oss</sub>		80		pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		4.9		
Gate Resistance	f = 1.0MHz	$R_g$		0.7		Ω
Switching (Note 4)						
Turn-On Delay Time		t <sub>d(on)</sub>		14		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 80V,$ $I_{D} = 4A, R_{G} = 2\Omega$	t <sub>r</sub>		21.4		
Turn-Off Delay Time		t <sub>d(off)</sub>		29.5		ns
Turn-Off Fall Time		t <sub>f</sub>		10.6		
Source-Drain Diode						
Forward Voltage (Note 3)	$V_{GS} = 0V, I_{S} = 11A$	V <sub>SD</sub>		0.8	1	V
Reverse Recovery Time	I <sub>S</sub> = 2A,	t <sub>rr</sub>		51		ns
Reverse Recovery Charge	dl/dt = 100A/μs	Q <sub>rr</sub>		3.2		nC

## Notes:

- 1. Current limited by package.
- 2. L = 0.3mH,  $V_{GS} = 10V$ ,  $V_{DD} = 80V$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^{\circ}C$
- 3. Pulse test: Pulse Width  $\leq$  300 $\mu$ s, duty cycle  $\leq$  2%.
- 4. Switching time is essentially independent of operating temperature.

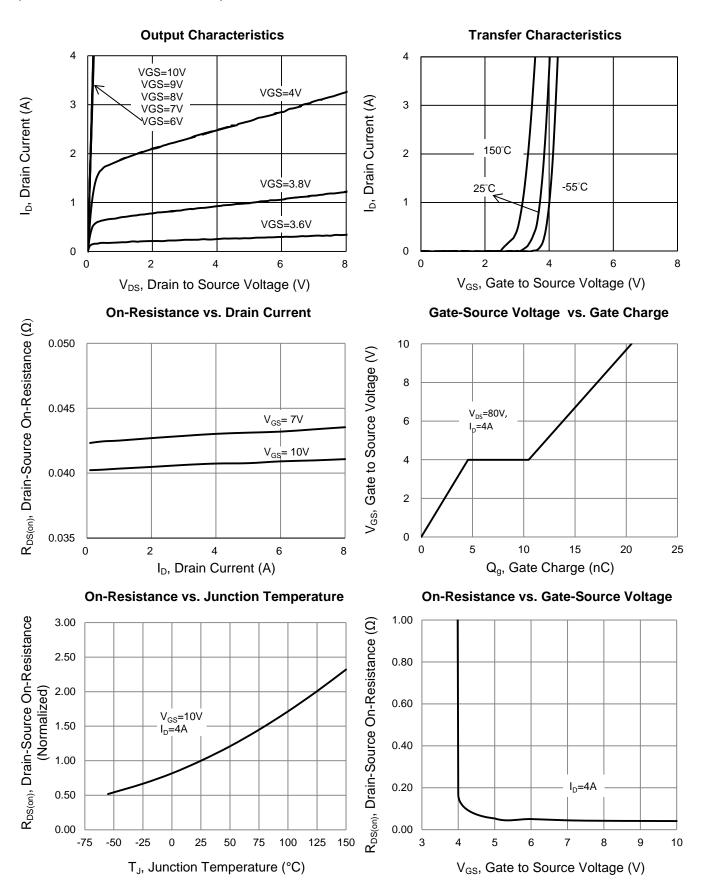
# **ORDERING INFORMATION**

ORDERING CODE	PACKAGE	PACKING
TSM500N15CS RLG	SOP-8	2,500pcs / 13" Reel



## **CHARACTERISTICS CURVES**

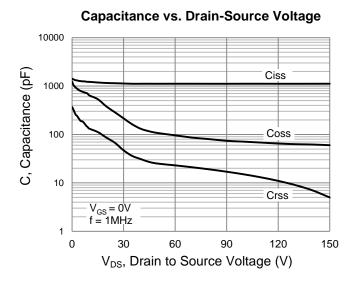
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

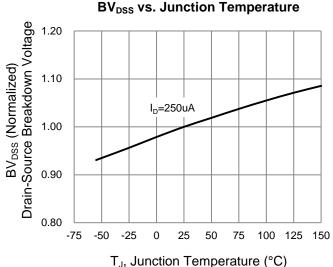




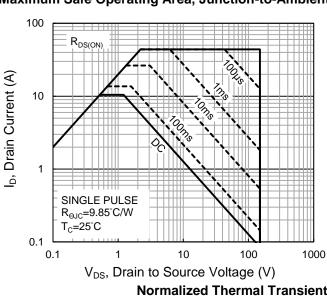
#### **CHARACTERISTICS CURVES**

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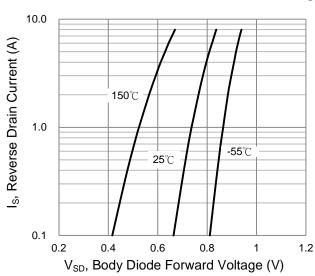




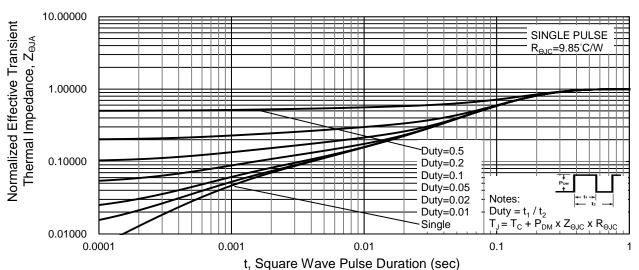
#### Maximum Safe Operating Area, Junction-to-Ambient



# Source-Drain Diode Forward Current vs. Voltage



Normalized Thermal Transient Impedance, Junction-to-Ambient



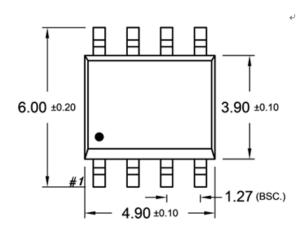
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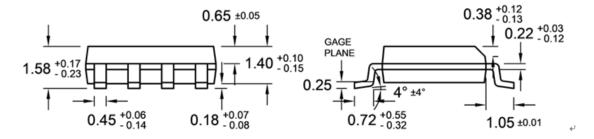
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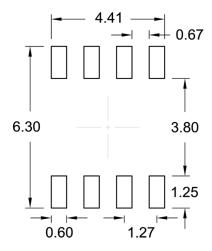
# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

## SOP-8





# SUGGESTED PAD LAYOUT (Unit: Millimeters)



# **MARKING DIAGRAM**



Y = Year Code

WW = Week Code (01~52)

L = Lot Code (1~9,A~Z)

F = Factory Code



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